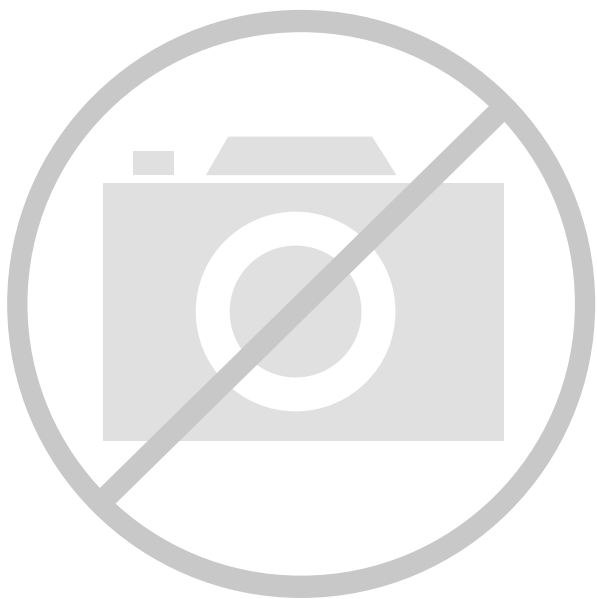




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	13824
Total RAM Bits	110592
Number of I/O	165
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agle600v2-fgg256i

Temperature Grade Offerings

Package	AGLE600	AGLE3000
		M1AGLPE3000
FG256	C, I	–
FG484	C, I	C, I
FG896	–	C, I

Note: C = Commercial temperature range: 0°C to 70°C ambient temperature.
 I = Industrial temperature range: –40°C to 85°C ambient temperature.

References made to IGLOOe devices also apply to ARM-enabled IGLOOe devices. The ARM-enabled part numbers start with M1 (Cortex-M1).

Contact your local Microsemi SoC Products Group representative for device availability:

<http://www.microsemi.com/soc/contact/default.aspx>.

Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature¹

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T _{STG} (°C) ²	Maximum Operating Junction Temperature T _J (°C) ²
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. This is a stress rating only; functional operation at any condition other than those indicated is not implied.
2. These limits apply for program/data retention only. Refer to [Table 2-1 on page 2-1](#) and [Table 2-2 for device operating conditions and absolute limits](#).

Table 2-4 • Overshoot and Undershoot Limits^{1, 3}

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at junction temperature at 85°C.
2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
3. This table does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every IGLOOe device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-1 on page 2-4](#) and [Figure 2-2 on page 2-5](#).

There are five regions to consider during power-up.

IGLOOe I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-1 on page 2-4](#) and [Figure 2-2 on page 2-5](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.2 V

Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.1 V

Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-19 on page 2-15](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-19 on page 2-15](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-19 on page 2-15](#).

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution— $P_{OUTPUTS}$

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * PAC10 * F_{CLK}$$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-19 on page 2-15](#).

β_1 is the I/O buffer enable rate—guidelines are provided in [Table 2-20 on page 2-15](#).

F_{CLK} is the global clock signal frequency.

RAM Contribution— P_{MEMORY}

$$P_{MEMORY} = PAC11 * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + PAC12 * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations—guidelines are provided in [Table 2-20 on page 2-15](#).

$F_{WRITE-CLOCK}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in [Table 2-20 on page 2-15](#).

PLL Contribution— P_{PLL}

$$P_{PLL} = PDC4 + PAC13 * F_{CLKOUT}$$

F_{CLKOUT} is the output clock frequency.¹

1. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($PAC13 * F_{CLKOUT}$ product) to the total PLL contribution.

Table 2-28 • I/O Output Buffer Maximum Resistances¹ (continued)

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75
3.3 V GTL	20 mA ⁵	11	—
2.5 V GTL	20 mA ⁵	14	—
3.3 V GTL+	35 mA	12	—
2.5 V GTL+	33 mA	15	—
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA	25	25
SSTL2 (I)	15 mA	27	31
SSTL2 (II)	18 mA	13	15
SSTL3 (I)	14 mA	44	69
SSTL3 (II)	21 mA	18	32

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at <http://www.microsemi.com/soc/techdocs/models/ibis.html>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / IOL_{spec}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / IOH_{spec}$
4. Applicable to IGLOOe V2 devices operating in the 1.2 V core range ONLY.
5. Output drive strength is below JEDEC specification.

**Table 2-29 • I/O Weak Pull-Up/Pull-Down Resistances
Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values**

VCCI	R _(WEAK PULL-UP) ¹ (Ω)		R _(WEAK PULL-DOWN) ² (Ω)	
	Minimum	Maximum	Minimum	Maximum
3.3 V	10 k	45 k	10 k	45 k
3.3 V (wide range I/Os)	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k
1.2 V	25 k	110 k	25 k	150 k
1.2 V (wide range I/Os)	19 k	110 k	19 k	150 k

Notes:

1. $R_{(WEAK PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / I_{(WEAK PULL-UP-MIN)}$
2. $R_{(WEAK PULL-DOWN-MAX)} = (VOL_{spec}) / I_{(WEAK PULL-DOWN-MIN)}$

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Equivalent Software Default Drive Strength Option ³	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	Min. (V)	μA	μA	Max. (mA) ⁴	Max. (mA) ⁴	μA ⁵	μA ⁵
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	12 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	103	109	10	10
100 μA	16 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	132	127	10	10
100 μA	24 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	268	181	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
4. Currents are measured at 85°C junction temperature.
5. All LVCMOS 3.3 V software macros supports LVCMOS 3.3 V wide range as specified in the JDEC8a specification.
6. Software default selection highlighted in gray.

Table 2-41 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	3.3	1.4	—	5

Note: *Measuring point = V_{trip} . See [Table 2-23 on page 2-23](#) for a complete table of trip points.

SSTL2 Class II

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). IGLOOe devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-101 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
18 mA	−0.3	VREF − 0.2	VREF + 0.2	3.6	0.35	VCCI − 0.43	18	18	169	124	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operating conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.

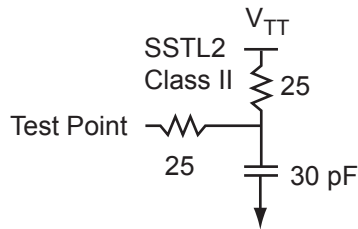


Figure 2-20 • AC Loading

Table 2-102 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input HIGH (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.2	VREF + 0.2	1.25	1.25	1.25	30

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-23 for a complete table of trip points.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-103 • SSTL 2 Class II – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 2.3 V VREF = 1.25 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.98	1.94	0.19	1.15	0.67	1.97	1.66			5.60	5.29	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-104 • SSTL 2 Class II – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 2.3 V VREF = 1.25 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	1.55	2.20	0.26	1.39	1.10	2.24	1.97			8.05	7.78	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Output Enable Register

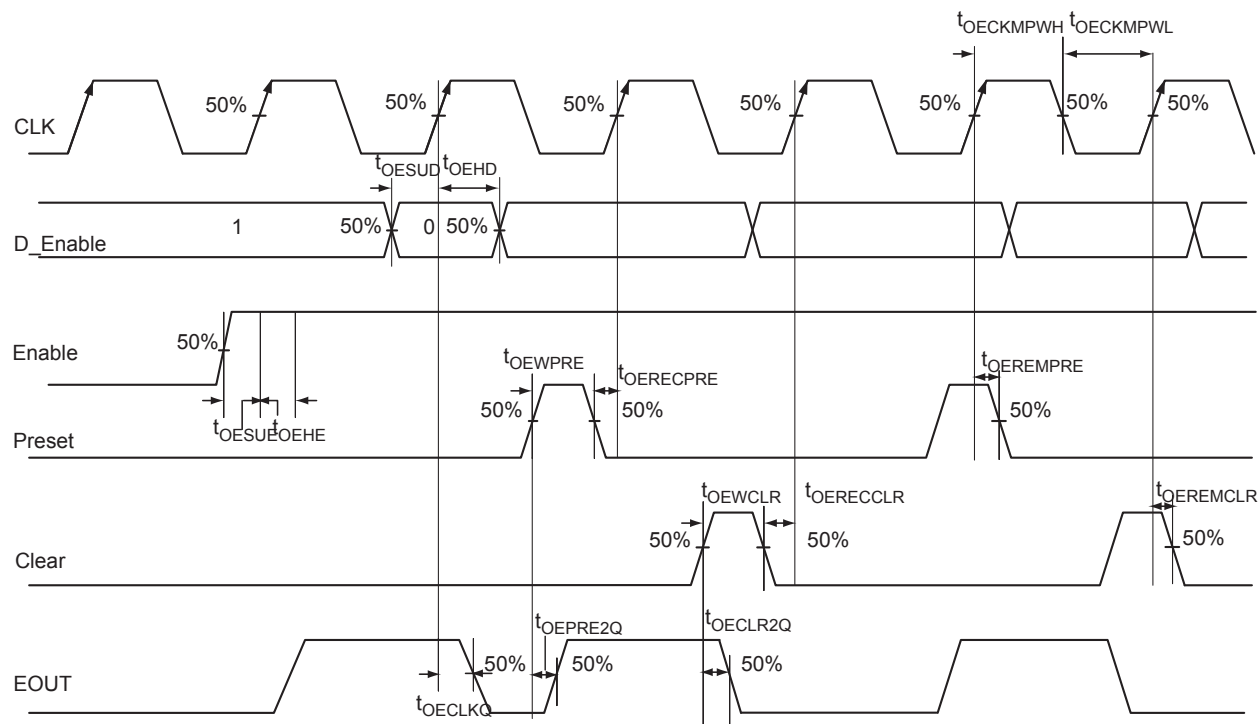


Figure 2-30 • Output Enable Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-127 • Output Enable Register Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.75	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.51	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.73	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.13	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.13	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPPE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width HIGH for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width LOW for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-133 • Output DDR Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.07	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.67	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.67	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDRORECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width HIGH for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width LOW for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

1.2 V DC Core Voltage

Table 2-134 • Output DDR Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.60	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	1.09	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	1.16	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.99	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDRORECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.24	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width HIGH for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width LOW for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

Embedded SRAM and FIFO Characteristics

SRAM

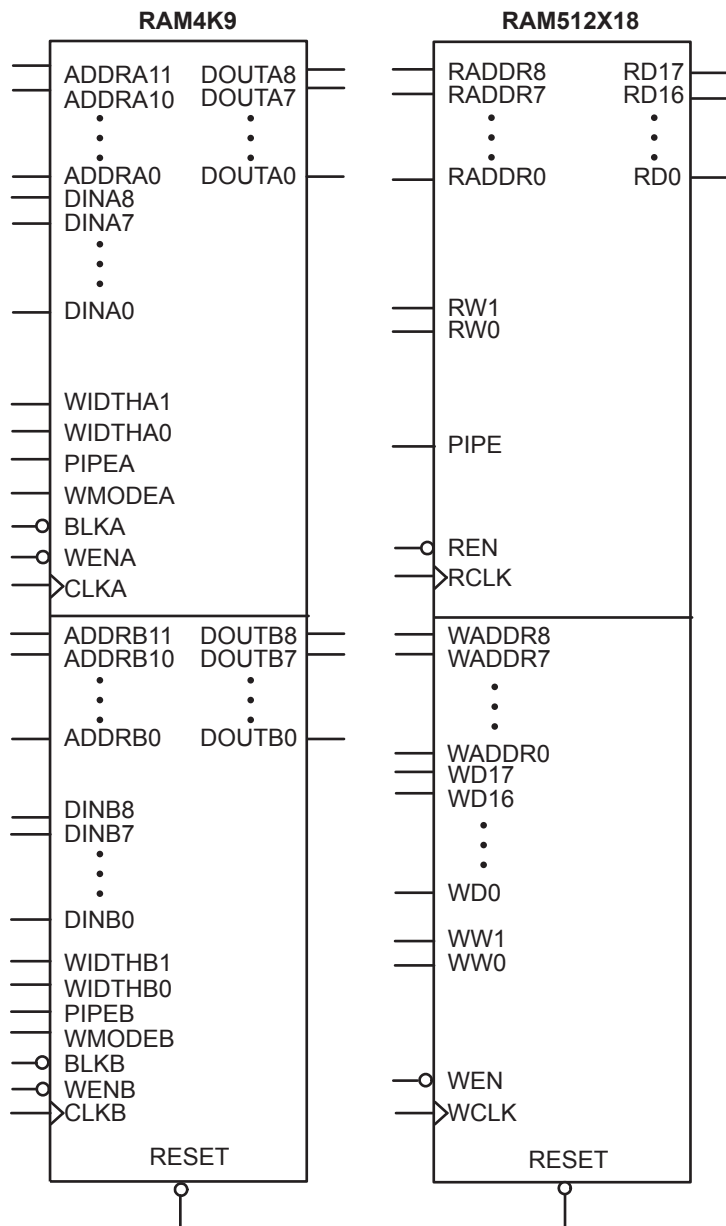


Figure 2-41 • RAM Models

FIFO

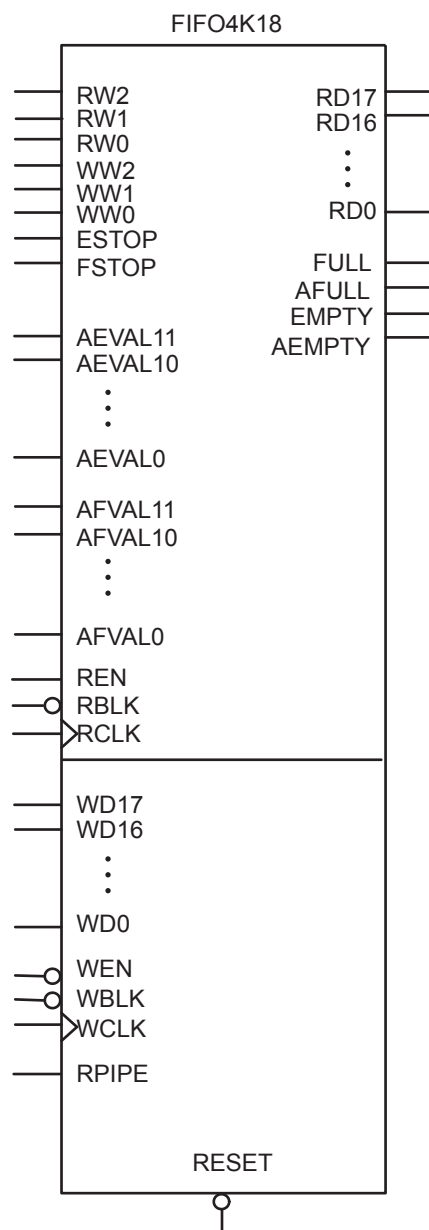


Figure 2-47 • FIFO Model

Table 3-3 • TRST and TCK Pull-Down Recommendations

VJTAG	Tie-Off Resistance*
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Note: Equivalent parallel resistance if more than one device is on the JTAG chain

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST Boundary Scan Reset Pin

The TRST pin functions as an active-low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from [Table 3-2](#) and must satisfy the parallel resistance value requirement. The values in [Table 3-2](#) correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements.

Special Function Pins

NC No Connect

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC Do Not Connect

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

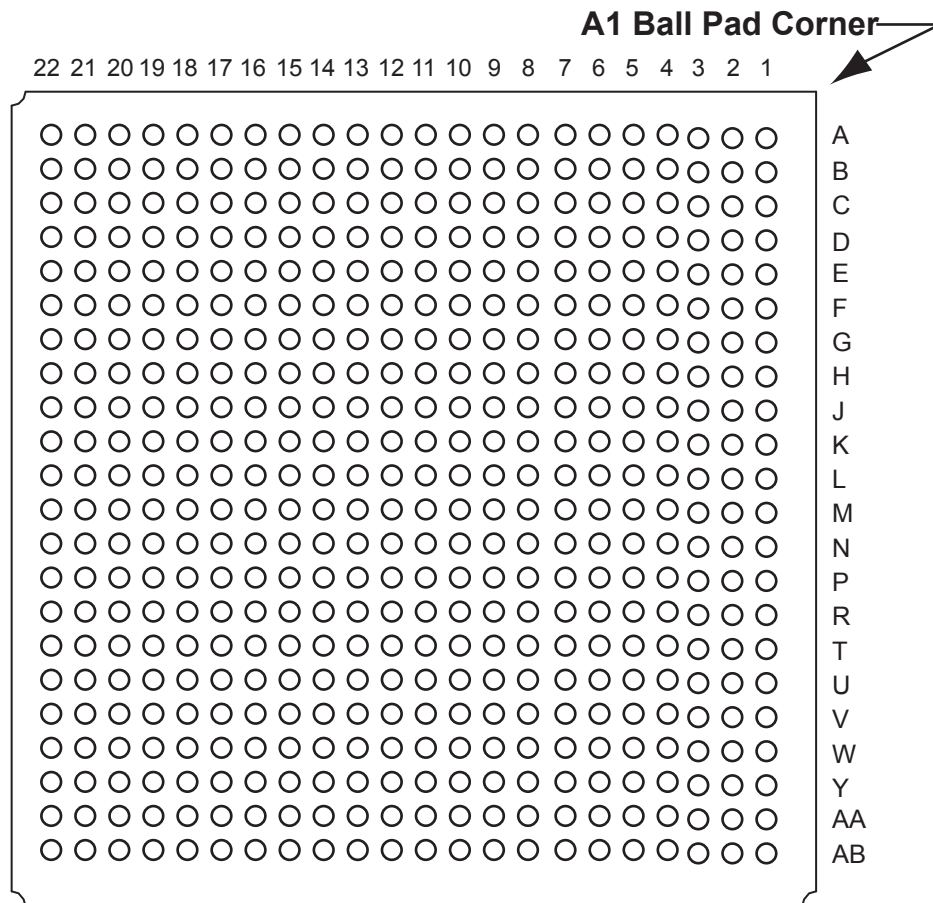
Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

FG256		FG256		FG256	
Pin Number	AGLE600 Function	Pin Number	AGLE600 Function	Pin Number	AGLE600 Function
G13	GCC1/IO50PPB2V1	K1	GFC2/IO115PSB6V1	M5	VMV5
G14	IO44NDB2V1	K2	IO113PPB6V1	M6	VCCIB5
G15	IO44PDB2V1	K3	IO112PDB6V1	M7	VCCIB5
G16	IO49NSB2V1	K4	IO112NDB6V1	M8	IO84NDB5V0
H1	GFB0/IO119NPB7V0	K5	VCCIB6	M9	IO84PDB5V0
H2	GFA0/IO118NDB6V1	K6	VCC	M10	VCCIB4
H3	GFB1/IO119PPB7V0	K7	GND	M11	VCCIB4
H4	VCOMPLF	K8	GND	M12	VMV3
H5	GFC0/IO120NPB7V0	K9	GND	M13	VCCPLD
H6	VCC	K10	GND	M14	GDB1/IO66PPB3V1
H7	GND	K11	VCC	M15	GDC1/IO65PDB3V1
H8	GND	K12	VCCIB3	M16	IO61NDB3V1
H9	GND	K13	IO54NPB3V0	N1	IO105PDB6V0
H10	GND	K14	IO57NPB3V0	N2	IO105NDB6V0
H11	VCC	K15	IO55NPB3V0	N3	GEC1/IO104PPB6V0
H12	GCC0/IO50NPB2V1	K16	IO57PPB3V0	N4	VCOMPLE
H13	GCB1/IO51PPB2V1	L1	IO113NPB6V1	N5	GNDQ
H14	GCA0/IO52NPB3V0	L2	IO109PPB6V0	N6	GEA2/IO101PPB5V2
H15	VCOMPLC	L3	IO108PDB6V0	N7	IO92NDB5V1
H16	GCB0/IO51NPB2V1	L4	IO108NDB6V0	N8	IO90NDB5V1
J1	GFA2/IO117PSB6V1	L5	VCCIB6	N9	IO82NDB5V0
J2	GFA1/IO118PDB6V1	L6	GND	N10	IO74NDB4V1
J3	VCCPLF	L7	VCC	N11	IO74PDB4V1
J4	IO116NDB6V1	L8	VCC	N12	GNDQ
J5	GFB2/IO116PDB6V1	L9	VCC	N13	VCOMPLD
J6	VCC	L10	VCC	N14	VJTAG
J7	GND	L11	GND	N15	GDC0/IO65NDB3V1
J8	GND	L12	VCCIB3	N16	GDA1/IO67PDB3V1
J9	GND	L13	GDB0/IO66NPB3V1	P1	GEB1/IO103PDB6V0
J10	GND	L14	IO60NDB3V1	P2	GEB0/IO103NDB6V0
J11	VCC	L15	IO60PDB3V1	P3	VMV6
J12	GCB2/IO54PPB3V0	L16	IO61PDB3V1	P4	VCCPLE
J13	GCA1/IO52PPB3V0	M1	IO109NPB6V0	P5	IO101NPB5V2
J14	GCC2/IO55PPB3V0	M2	IO106NDB6V0	P6	IO95PPB5V1
J15	VCCPLC	M3	IO106PDB6V0	P7	IO92PDB5V1
J16	GCA2/IO53PSB3V0	M4	GEC0/IO104NPB6V0	P8	IO90PDB5V1

FG484



Note: This is the bottom view of the package.

Note

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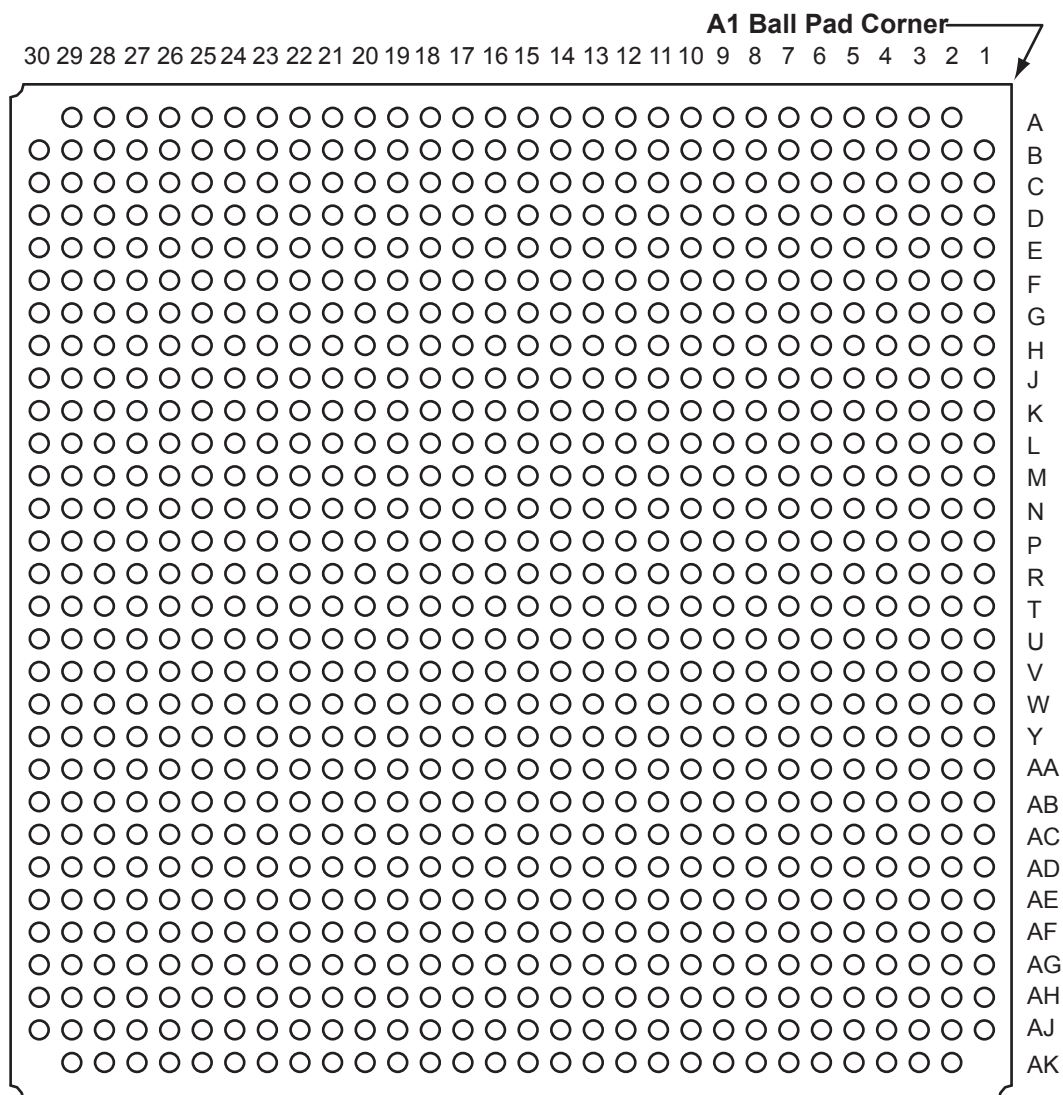
FG484		FG484		FG484	
Pin Number	AGLE600 Function	Pin Number	AGLE600 Function	Pin Number	AGLE600 Function
A1	GND	AA14	NC	B5	IO03PDB0V0
A2	GND	AA15	NC	B6	IO07NDB0V1
A3	VCCIB0	AA16	IO71NDB4V0	B7	IO07PDB0V1
A4	IO06NDB0V1	AA17	IO71PDB4V0	B8	IO11NDB0V1
A5	IO06PDB0V1	AA18	NC	B9	IO17NDB0V2
A6	IO08NDB0V1	AA19	NC	B10	IO14PDB0V2
A7	IO08PDB0V1	AA20	NC	B11	IO19PDB0V2
A8	IO11PDB0V1	AA21	VCCIB3	B12	IO22NDB1V0
A9	IO17PDB0V2	AA22	GND	B13	IO26NDB1V0
A10	IO18NDB0V2	AB1	GND	B14	NC
A11	IO18PDB0V2	AB2	GND	B15	NC
A12	IO22PDB1V0	AB3	VCCIB5	B16	IO30NDB1V1
A13	IO26PDB1V0	AB4	IO97NDB5V2	B17	IO30PDB1V1
A14	IO29NDB1V1	AB5	IO97PDB5V2	B18	IO32PDB1V1
A15	IO29PDB1V1	AB6	IO93NDB5V1	B19	NC
A16	IO31NDB1V1	AB7	IO93PDB5V1	B20	NC
A17	IO31PDB1V1	AB8	IO87NDB5V0	B21	VCCIB2
A18	IO32NDB1V1	AB9	IO87PDB5V0	B22	GND
A19	NC	AB10	NC	C1	VCCIB7
A20	VCCIB1	AB11	NC	C2	NC
A21	GND	AB12	IO75NDB4V1	C3	NC
A22	GND	AB13	IO75PDB4V1	C4	NC
AA1	GND	AB14	IO72NDB4V0	C5	GND
AA2	VCCIB6	AB15	IO72PDB4V0	C6	IO04NDB0V0
AA3	NC	AB16	IO73NDB4V0	C7	IO04PDB0V0
AA4	IO98PDB5V2	AB17	IO73PDB4V0	C8	VCC
AA5	IO96NDB5V2	AB18	NC	C9	VCC
AA6	IO96PDB5V2	AB19	NC	C10	IO14NDB0V2
AA7	IO86NDB5V0	AB20	VCCIB4	C11	IO19NDB0V2
AA8	IO86PDB5V0	AB21	GND	C12	NC
AA9	IO85PDB5V0	AB22	GND	C13	NC
AA10	IO85NDB5V0	B1	GND	C14	VCC
AA11	IO78PPB4V1	B2	VCCIB7	C15	VCC
AA12	IO79NDB4V1	B3	NC	C16	NC
AA13	IO79PDB4V1	B4	IO03NDB0V0	C17	NC

FG484		FG484		FG484	
Pin Number	AGLE600 Function	Pin Number	AGLE600 Function	Pin Number	AGLE600 Function
C18	GND	E9	IO10NDB0V1	F22	NC
C19	NC	E10	IO12NDB0V2	G1	IO127NDB7V1
C20	NC	E11	IO16PDB0V2	G2	IO127PDB7V1
C21	NC	E12	IO20NDB1V0	G3	NC
C22	VCCIB2	E13	IO24NDB1V0	G4	IO128PDB7V1
D1	NC	E14	IO24PDB1V0	G5	IO129PDB7V1
D2	NC	E15	GBC1/IO33PDB1V1	G6	GAC2/IO132PDB7V1
D3	NC	E16	GBB0/IO34NDB1V1	G7	VCOMPLA
D4	GND	E17	GNDQ	G8	GNDQ
D5	GAA0/IO00NDB0V0	E18	GBA2/IO36PDB2V0	G9	IO09NDB0V1
D6	GAA1/IO00PDB0V0	E19	IO42NDB2V0	G10	IO09PDB0V1
D7	GAB0/IO01NDB0V0	E20	GND	G11	IO13PDB0V2
D8	IO05PDB0V0	E21	NC	G12	IO21PDB1V0
D9	IO10PDB0V1	E22	NC	G13	IO25PDB1V0
D10	IO12PDB0V2	F1	NC	G14	IO27NDB1V0
D11	IO16NDB0V2	F2	IO131NDB7V1	G15	GNDQ
D12	IO23NDB1V0	F3	IO131PDB7V1	G16	VCOMPLB
D13	IO23PDB1V0	F4	IO133NDB7V1	G17	GBB2/IO37PDB2V0
D14	IO28NDB1V1	F5	IO134NDB7V1	G18	IO39PDB2V0
D15	IO28PDB1V1	F6	VMV7	G19	IO39NDB2V0
D16	GBB1/IO34PDB1V1	F7	VCCPLA	G20	IO43PDB2V0
D17	GBA0/IO35NDB1V1	F8	GAC0/IO02NDB0V0	G21	IO43NDB2V0
D18	GBA1/IO35PDB1V1	F9	GAC1/IO02PDB0V0	G22	NC
D19	GND	F10	IO15NDB0V2	H1	NC
D20	NC	F11	IO15PDB0V2	H2	NC
D21	NC	F12	IO20PDB1V0	H3	VCC
D22	NC	F13	IO25NDB1V0	H4	IO128NDB7V1
E1	NC	F14	IO27PDB1V0	H5	IO129NDB7V1
E2	NC	F15	GBC0/IO33NDB1V1	H6	IO132NDB7V1
E3	GND	F16	VCCPLB	H7	IO130PDB7V1
E4	GAB2/IO133PDB7V1	F17	VMV2	H8	VMV0
E5	GAA2/IO134PDB7V1	F18	IO36NDB2V0	H9	VCCIB0
E6	GNDQ	F19	IO42PDB2V0	H10	VCCIB0
E7	GAB1/IO01PDB0V0	F20	NC	H11	IO13NDB0V2
E8	IO05NDB0V0	F21	NC	H12	IO21NDB1V0

FG484	
Pin Number	AGLE3000 Function
V3	GND
V4	GEA1/IO234PDB6V0
V5	GEA0/IO234NDB6V0
V6	GNDQ
V7	GEC2/IO231PDB5V4
V8	IO222NPB5V3
V9	IO204NDB5V1
V10	IO204PDB5V1
V11	IO195NDB5V0
V12	IO195PDB5V0
V13	IO178NDB4V3
V14	IO178PDB4V3
V15	IO155NDB4V0
V16	GDB2/IO155PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	IO146PDB3V4
V22	IO142NDB3V3
W1	IO239NDB6V0
W2	IO237PDB6V0
W3	IO230PSB5V4
W4	GND
W5	IO232NDB5V4
W6	FF/GEB2/IO232PDB5V4
W7	IO231NDB5V4
W8	IO214NDB5V2
W9	IO214PDB5V2
W10	IO200NDB5V0
W11	IO192NDB4V4
W12	IO184NDB4V3
W13	IO184PDB4V3
W14	IO156NDB4V0

FG484	
Pin Number	AGLE3000 Function
W15	GDC2/IO156PDB4V0
W16	IO154NDB4V0
W17	GDA2/IO154PDB4V0
W18	TMS
W19	GND
W20	IO150NDB3V4
W21	IO146NDB3V4
W22	IO148PPB3V4
Y1	VCCIB6
Y2	IO237NDB6V0
Y3	IO228NDB5V4
Y4	IO224NDB5V3
Y5	GND
Y6	IO220NDB5V3
Y7	IO220PDB5V3
Y8	VCC
Y9	VCC
Y10	IO200PDB5V0
Y11	IO192PDB4V4
Y12	IO188NPB4V4
Y13	IO187PSB4V4
Y14	VCC
Y15	VCC
Y16	IO164NDB4V1
Y17	IO164PDB4V1
Y18	GND
Y19	IO158PPB4V0
Y20	IO150PDB3V4
Y21	IO148NPB3V4
Y22	VCCIB3

FG896



Note: This is the bottom view of the package.

Note

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FG896	
Pin Number	AGLE3000 Function
L26	IO87NDB2V0
L27	IO97PDB2V1
L28	IO101PDB2V2
L29	IO103PDB2V2
L30	IO119NDB3V0
M1	IO282NDB7V1
M2	IO282PDB7V1
M3	IO292NDB7V2
M4	IO292PDB7V2
M5	IO283NDB7V1
M6	IO285PDB7V1
M7	IO287PDB7V1
M8	IO289PDB7V1
M9	IO289NDB7V1
M10	VCCIB7
M11	VCC
M12	GND
M13	GND
M14	GND
M15	GND
M16	GND
M17	GND
M18	GND
M19	GND
M20	VCC
M21	VCCIB2
M22	NC
M23	IO104PPB2V2
M24	IO102PDB2V2
M25	IO102NDB2V2
M26	IO95PDB2V1
M27	IO97NDB2V1
M28	IO101NDB2V2
M29	IO103NDB2V2
M30	IO119PDB3V0

FG896	
Pin Number	AGLE3000 Function
N1	IO276PDB7V0
N2	IO278PDB7V0
N3	IO280PDB7V0
N4	IO284PDB7V1
N5	IO279PDB7V0
N6	IO285NDB7V1
N7	IO287NDB7V1
N8	IO281NDB7V0
N9	IO281PDB7V0
N10	VCCIB7
N11	VCC
N12	GND
N13	GND
N14	GND
N15	GND
N16	GND
N17	GND
N18	GND
N19	GND
N20	VCC
N21	VCCIB2
N22	IO106NDB2V3
N23	IO106PDB2V3
N24	IO108PDB2V3
N25	IO108NDB2V3
N26	IO95NDB2V1
N27	IO99NDB2V2
N28	IO99PDB2V2
N29	IO107PDB2V3
N30	IO107NDB2V3
P1	IO276NDB7V0
P2	IO278NDB7V0
P3	IO280NDB7V0
P4	IO284NDB7V1
P5	IO279NDB7V0

FG896	
Pin Number	AGLE3000 Function
P6	GFC1/IO275PDB7V0
P7	GFC0/IO275NDB7V0
P8	IO277PDB7V0
P9	IO277NDB7V0
P10	VCCIB7
P11	VCC
P12	GND
P13	GND
P14	GND
P15	GND
P16	GND
P17	GND
P18	GND
P19	GND
P20	VCC
P21	VCCIB2
P22	GCC1/IO112PDB2V3
P23	IO110PDB2V3
P24	IO110NDB2V3
P25	IO109PPB2V3
P26	IO111NPB2V3
P27	IO105PDB2V2
P28	IO105NDB2V2
P29	GCC2/IO117PDB3V0
P30	IO117NDB3V0
R1	GFC2/IO270PDB6V4
R2	GFB1/IO274PPB7V0
R3	VCOMPLF
R4	GFA0/IO273NDB6V4
R5	GFB0/IO274NPB7V0
R6	IO271NDB6V4
R7	GFB2/IO271PDB6V4
R8	IO269PDB6V4
R9	IO269NDB6V4
R10	VCCIB7

FG896	
Pin Number	AGLE3000 Function
V26	IO126NDB3V1
V27	IO129NDB3V1
V28	IO127NDB3V1
V29	IO125NDB3V1
V30	IO123PDB3V1
W1	IO266NDB6V4
W2	IO262NDB6V3
W3	IO260NDB6V3
W4	IO252NDB6V2
W5	IO251NDB6V2
W6	IO251PDB6V2
W7	IO255NDB6V2
W8	IO249PPB6V1
W9	IO253PDB6V2
W10	VCCIB6
W11	VCC
W12	GND
W13	GND
W14	GND
W15	GND
W16	GND
W17	GND
W18	GND
W19	GND
W20	VCC
W21	VCCIB3
W22	IO134PDB3V2
W23	IO138PDB3V3
W24	IO132NDB3V2
W25	IO136NPB3V2
W26	IO130NPB3V2
W27	IO141PDB3V3
W28	IO135PDB3V2
W29	IO131PDB3V2
W30	IO123NDB3V1

FG896	
Pin Number	AGLE3000 Function
Y1	IO266PDB6V4
Y2	IO250PDB6V2
Y3	IO250NDB6V2
Y4	IO246PDB6V1
Y5	IO247NDB6V1
Y6	IO247PDB6V1
Y7	IO249NPB6V1
Y8	IO245PDB6V1
Y9	IO253NDB6V2
Y10	GEB0/IO235NPB6V0
Y11	VCC
Y12	VCC
Y13	VCC
Y14	VCC
Y15	VCC
Y16	VCC
Y17	VCC
Y18	VCC
Y19	VCC
Y20	VCC
Y21	IO142PPB3V3
Y22	IO134NDB3V2
Y23	IO138NDB3V3
Y24	IO140NDB3V3
Y25	IO140PDB3V3
Y26	IO136PPB3V2
Y27	IO141NDB3V3
Y28	IO135NDB3V2
Y29	IO131NDB3V2
Y30	IO133PDB3V2

Revision	Changes	Page
Revision 8 (Nov 2009)	The version changed to v2.0 for IGLOOe datasheet chapters, indicating the datasheet contains information based on final characterization.	N/A
Product Brief v2.0 DC and Switching Characteristics v2.0	The "Pro (Professional) I/O" section was revised to add "Hot-swappable and cold-sparing I/Os."	I
	The "Reprogrammable Flash Technology" section was revised to add "250 MHz (1.5 V systems) and 160 MHz (1.2 V systems) System Performance."	I
	Definitions of hot-swap and cold-sparing were added to the "Pro I/Os with Advanced I/O Standards" section.	1-7
	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A
	IIL and IIH input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A
	Values for 1.2 V wide range DC core supply voltage were added to Table 2-2 • Recommended Operating Conditions 1. Table notes regarding 3.3 V wide range and the core voltage required for programming were added to the table.	2-2
	The data in Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (1.5 V DC core supply voltage) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (1.2 V DC core supply voltage) was revised.	2-6
	3.3 V LVCMOS wide range data was included in Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings and Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings1. Table notes were added in connection with this data.	2-9, 2-10
	The temperature was revised from 110°C to 100°C in Table 2-31 • Duration of Short Circuit Event before Failure and Table 2-33 • I/O Input Rise Time, Fall Time, and Related I/O Reliability*.	2-31, 2-31
	The tables in the "Overview of I/O Performance" section and "Detailed I/O DC Characteristics" section were revised to include 3.3 V LVCMOS and 1.2 V LVCMOS wide range.	2-20, 2-28
	Most tables were updated in the following sections, revising existing values and adding information for 3.3 V and 1.2 V wide range: "Single-Ended I/O Characteristics" "Voltage-Referenced I/O Characteristics" "Differential I/O Characteristics"	2-32, 2-51, 2-62
	The value for "Delay range in block: fixed delay" was revised in Table 2-143 • IGLOOe CCC/PLL Specification and Table 2-144 • IGLOOe CCC/PLL Specification.	2-91, 2-92
	The timing characteristics tables for RAM4K9 and RAM512X18 were updated, including renaming of the address collision parameters.	2-98 – 2-101
Revision 7 (Apr 2009) Product Brief v1.4 DC and Switching Characteristics Advance v0.4	The –F speed grade is no longer offered for IGLOOe devices and was removed from the documentation. The speed grade column and note regarding –F speed grade were removed from "IGLOOe Ordering Information". The "Speed Grade and Temperature Grade Matrix" section was removed.	III, IV